

Product Summary

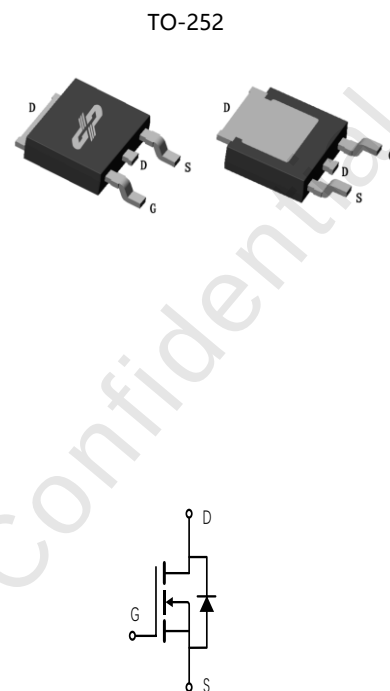
Part #	V_{DS}	$R_{DS(on)}$	I_D ($T_{vj}=25^{\circ}C$)
DPM065R400D3G2	800V	375m Ω	7A

Features

- High Speed Switching with Low Capacitances
- High Blocking Voltage with Low $R_{DS(on)}$
- Easy to parallel
- RoHS Compliant

Applications

- General purpose drives
- Energy storage systems
- String inverter
- Uninterruptible power supplies



Package Marking and Ordering Information

Part #	Marking	Package	Packing
DPM065R400D3G2	M065R400D3	TO-252	Tape/Reel



Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	800	V
Continuous drain current $T_C = 25^{\circ}C$ $T_C = 100^{\circ}C$	I_D	7 5.1	A
Pulsed drain current ($T_C = 25^{\circ}C$, t_p limited by T_{jmax})	$I_{D\ pulse}$	28	A
Gate-source voltage, max. transient voltage	V_{GSmax}	-10/+22	V
Gate-source voltage, operate voltage	V_{GSop}	0/+15	V
Power dissipation ($T_C = 25^{\circ}C$) Power dissipation ($T_C = 100^{\circ}C$)	P_{tot}	29 14	W
Operating junction temperature	T_j	-40...+175	$^{\circ}C$
Storage temperature	T_{stg}	-40...+175	$^{\circ}C$

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – mounting base	R_{thMB}	2.7	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	80	

Electrical Characteristic (at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	800	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate threshold voltage	$V_{GS(th)}$	3	3.8 2.7		V	$V_{DS}=V_{GS}, I_D=3.5mA$ $T_j=25^{\circ}\text{C}$ $T_j=175^{\circ}\text{C}$
Zero gate voltage drain current	I_{DSS}	-	0.1	20	μA	$V_{DS}=640V, V_{GS}=0V$ $T_j=25^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}	-	-	250	nA	$V_{GS}=18V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	375 384	470	m Ω	$V_{GS}=18V, I_D=4.0A$ $T_j=25^{\circ}\text{C}$ $T_j=175^{\circ}\text{C}$
		-	500 509	650	m Ω	$V_{GS}=15V, I_D=4.0A$ $T_j=25^{\circ}\text{C}$ $T_j=175^{\circ}\text{C}$
Gate resistance	R_g	-	35	-	Ω	$V_{GS}=0V, V_{DS}=0V,$ $f=1MHz$

Dynamic Characteristic^[2]

Input Capacitance	C_{iss}	-	145	-	pF	$V_{GS}=0V, V_{DS}=400V,$ $f=1MHz$
Output Capacitance	C_{oss}	-	11	-		
Reverse Transfer Capacitance	C_{rss}	-	0.9	-		
Gate Total Charge	Q_g	-	6.8	-	nC	$V_{GS}=0/15V, V_{DS}=400V,$ $I_D=4.0A, f=1MHz$
Gate-Source charge	Q_{gs}	-	2.9	-		
Gate-Drain charge	Q_{gd}	-	1.1	-		
Turn-on delay time	$t_{d(on)}$	-	15	-	ns	$V_{GS}=0/15V, V_{DD}=400V,$ $R_{G_ext}=2.5\Omega$ $L=200\mu H$
Rise time	t_r	-	14	-		
Turn-off delay time	$t_{d(off)}$	-	12	-		
Fall time	t_f	-	13.5	-		
Turn-On Energy	E_{on}	-	41	-	μJ	
Turn-Off Energy	E_{off}	-	3	-		

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	3.8 3.3	5.3	V	$V_{GS}=0V, I_{SD}=2.0A$ $T_j=25^{\circ}C$ $T_j=175^{\circ}C$
Diode continuous forward current	I_s		6 4.0	- -	A	$V_{GS}=0V$ $T_C = 25^{\circ}C$ $T_C = 100^{\circ}C$
Diode Peak reverse recovery Current	I_{rrm}	-	4.2	-	A	$V_{GS}=0V, V_R=400V$ $I_{SD}=4.0A, dI/dt=1100A/\mu s$
Body Diode Reverse Recovery Time ^[2]	t_{rr}	-	8	-	ns	
Body Diode Reverse Recovery Charge ^[2]	Q_{rr}	-	20	-	nC	

[2]. Defined by design. Not subject to production test

Typical Performance Characteristics

Fig 1: Output Characteristics

$T_j = -55^\circ\text{C}$

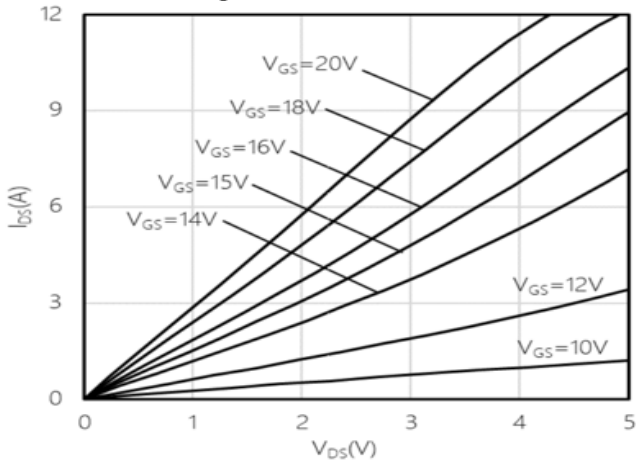


Fig 2: Output Characteristics

$T_j = 25^\circ\text{C}$

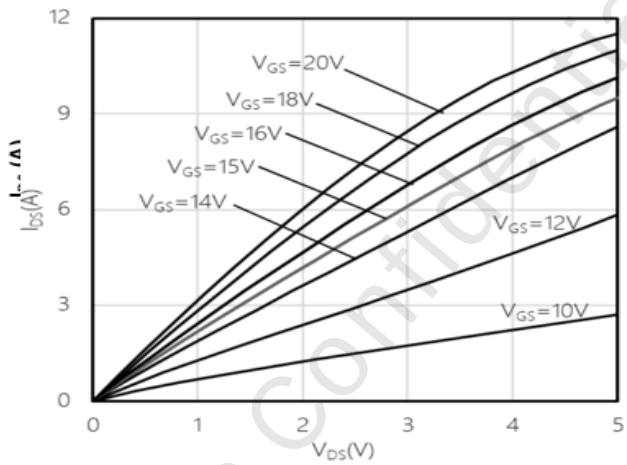


Fig 3: Output Characteristics

$T_j = 175^\circ\text{C}$

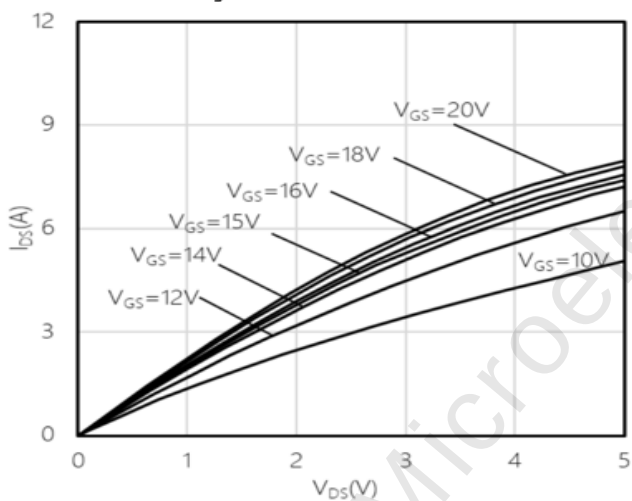


Fig 4: $R_{ds(on)}$ vs Drain Current for various Temperature

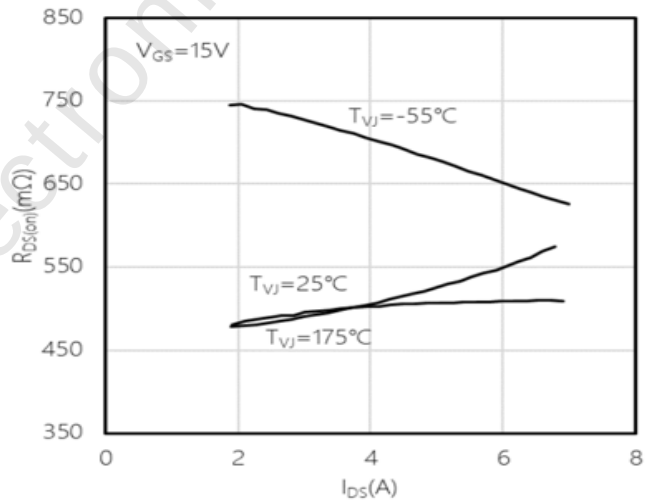


Fig 5: $R_{ds(on)}$ vs. Temperature

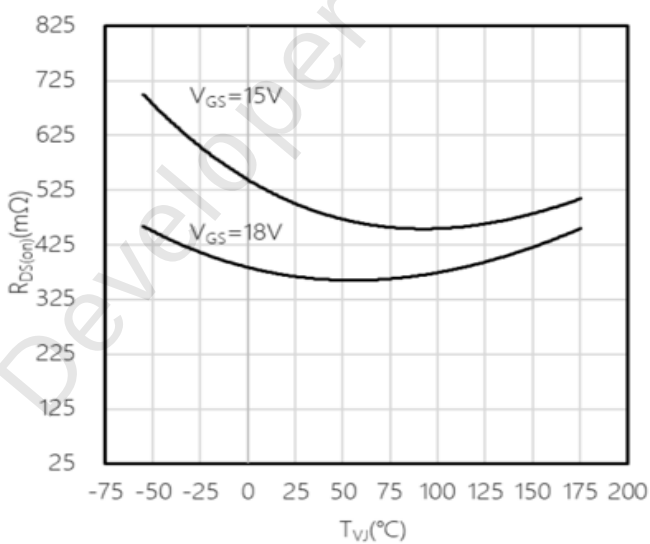
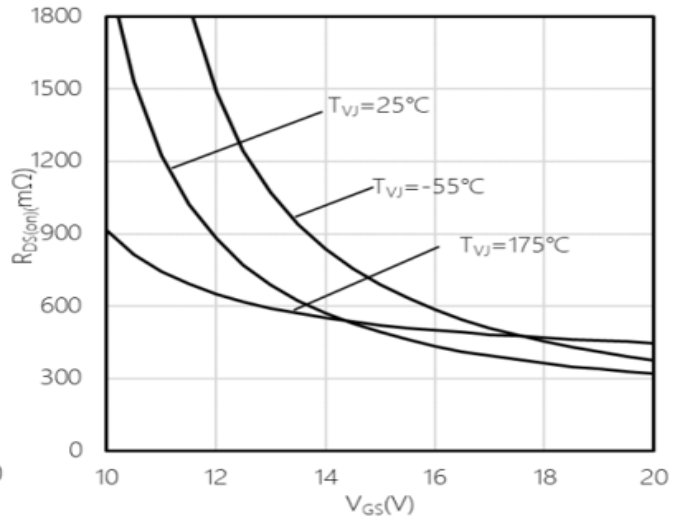


Fig 6: $R_{ds(on)}$ vs. Gate Voltage at Temperature



Typical Performance Characteristics

Fig 7: Transfer Characteristics

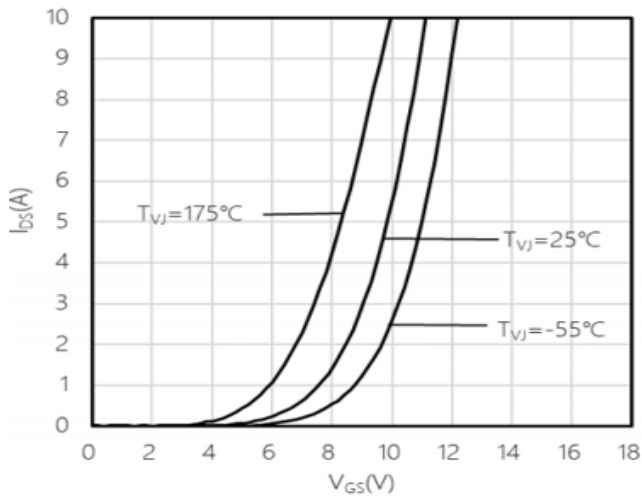


Fig 8: Body Diode Characteristic $T_j = -55^{\circ}\text{C}$

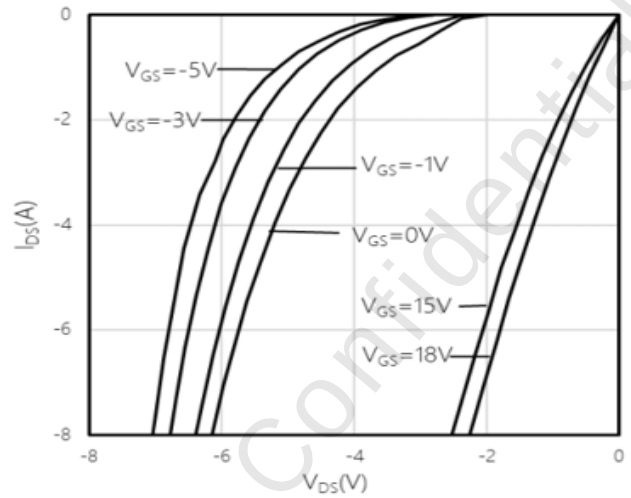


Fig 9: Body Diode Characteristic
 $T_i = 25^{\circ}\text{C}$

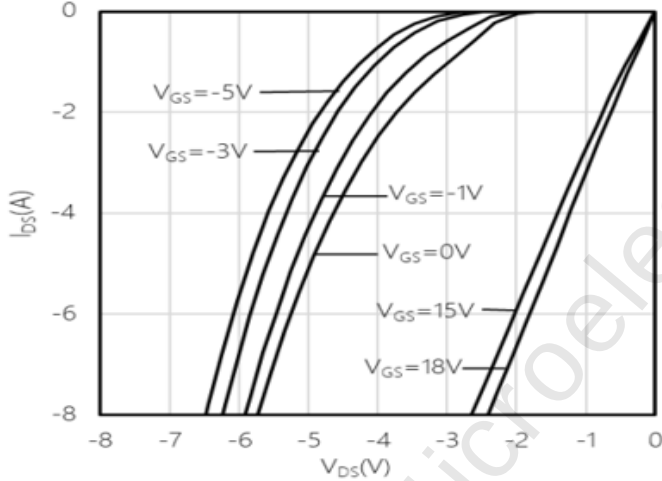


Fig 10: Body Diode Characteristic
 $T_i = 175^{\circ}\text{C}$

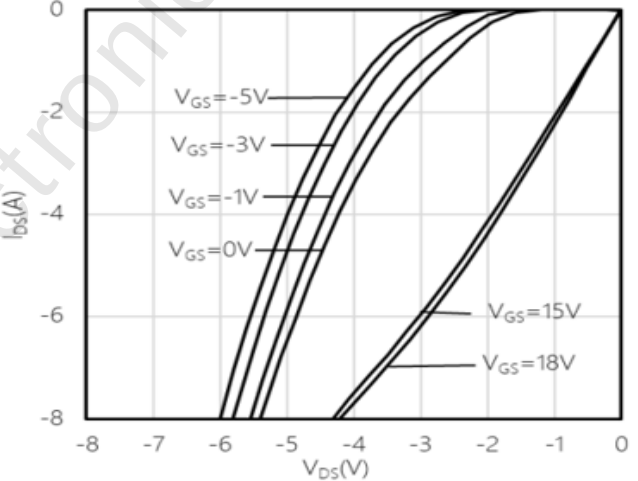


Fig 11: Threshold Voltage vs.
Temperature

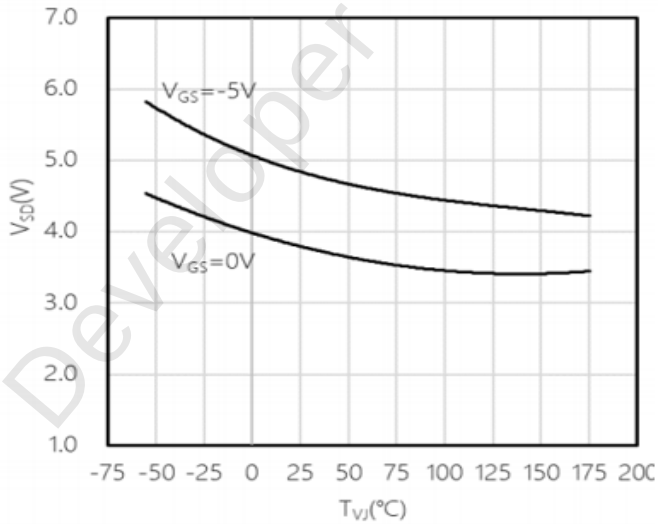


Fig 12: Capacitance Characteristics

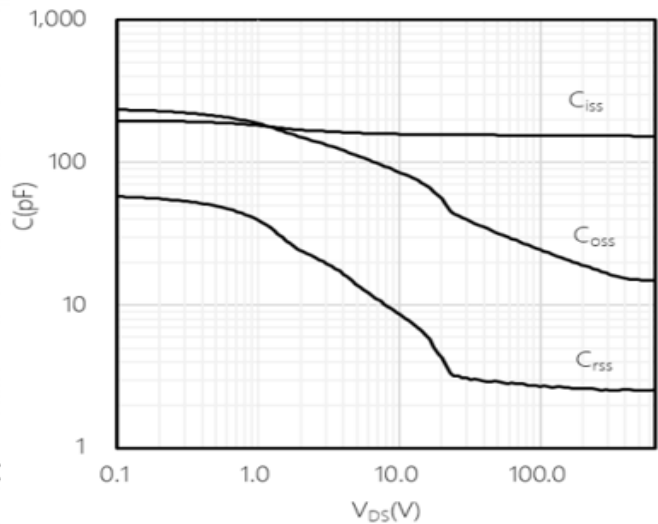


Fig 13: Gate Charge Characteristics

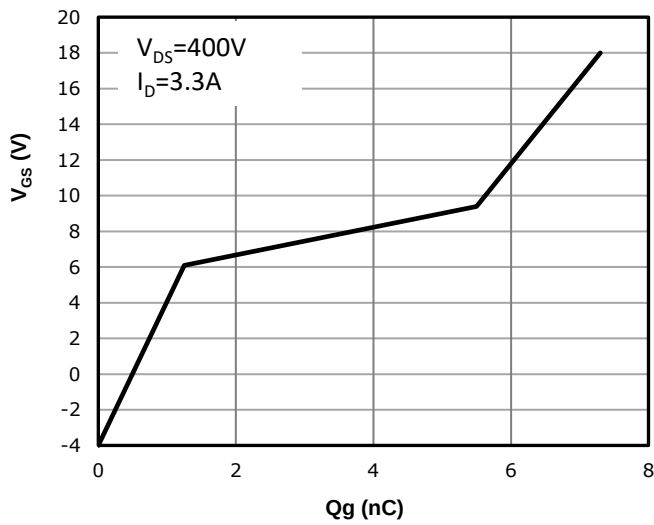


Fig 14: Clamped Inductive Switching energy vs R_g

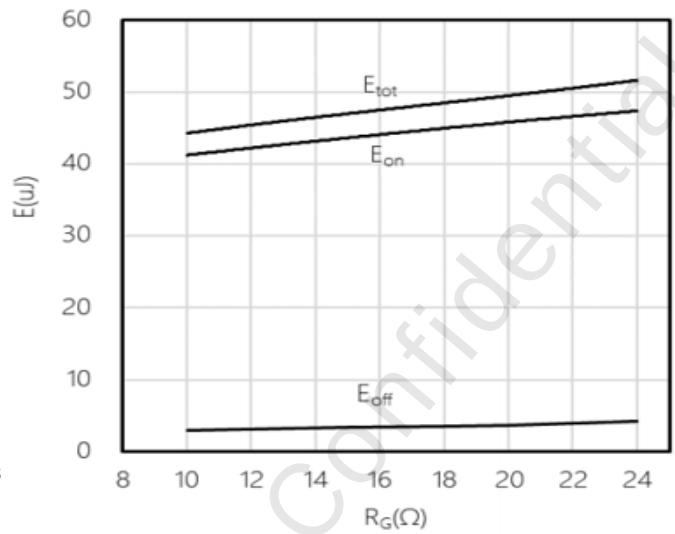


Fig 15: Power Dissipation

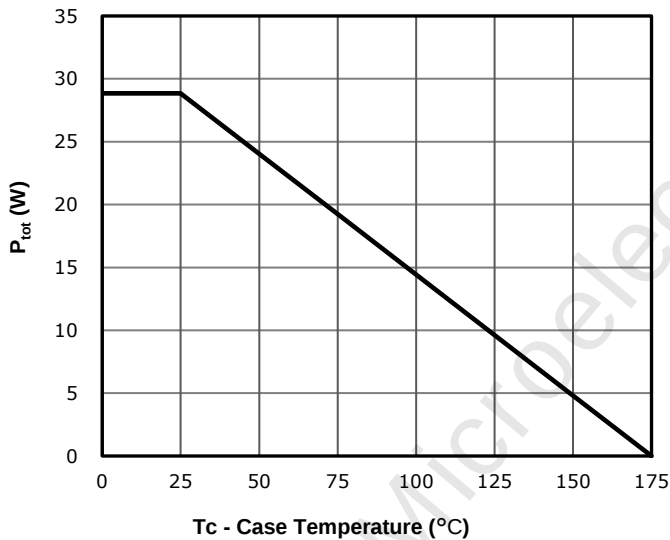


Fig 16: Drain Current Derating

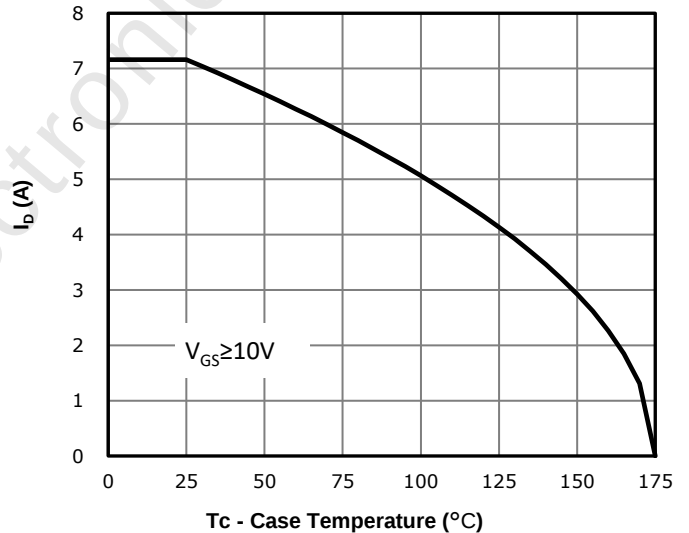


Fig 17: Safe Operating Area

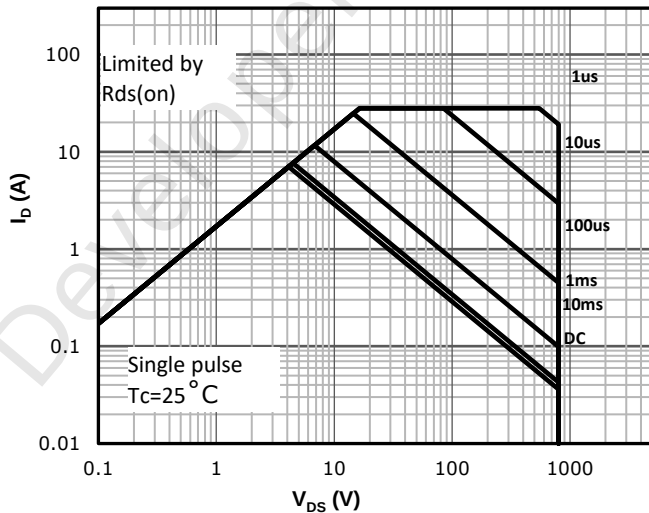
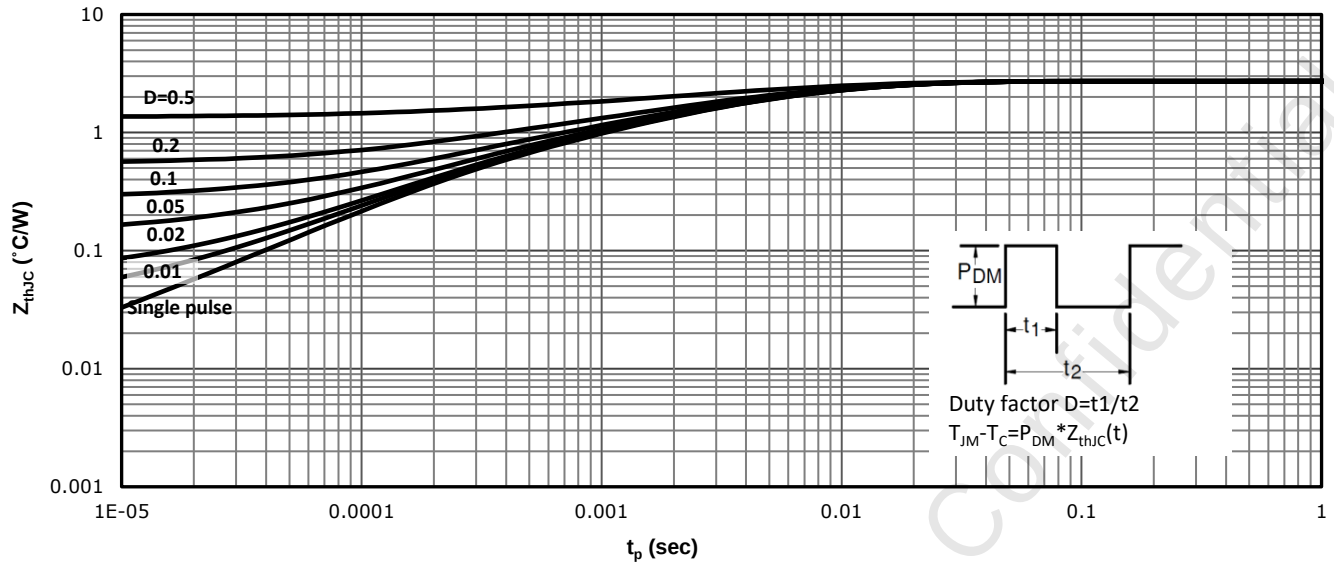
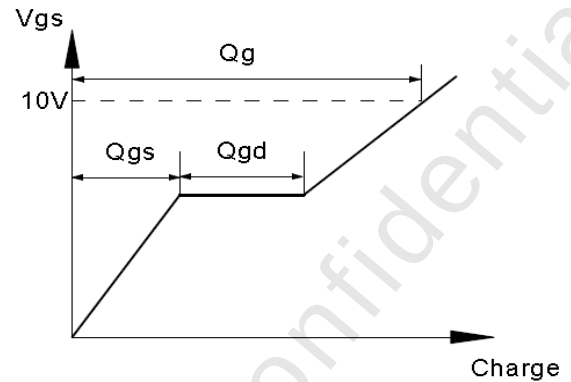
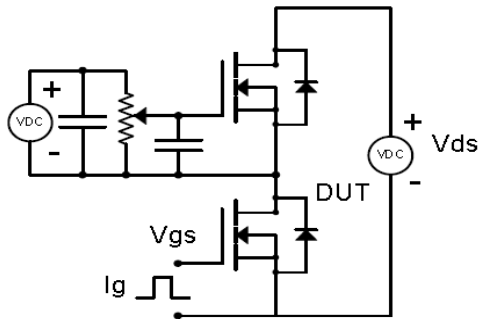


Fig 18: Max. Transient Thermal Impedance

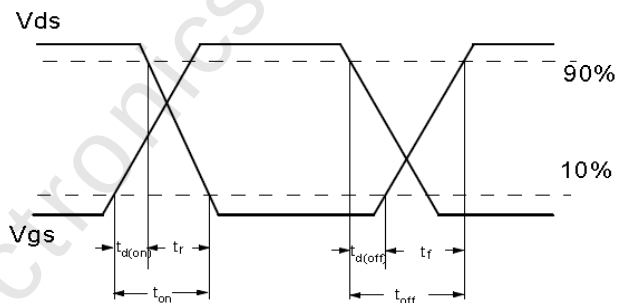
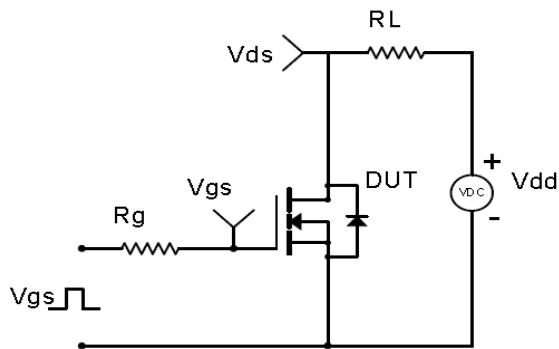


Test Circuit & Waveform

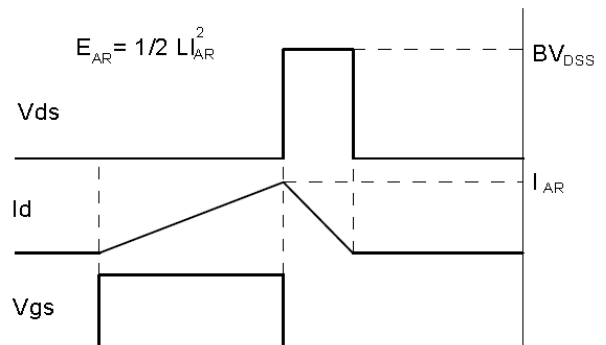
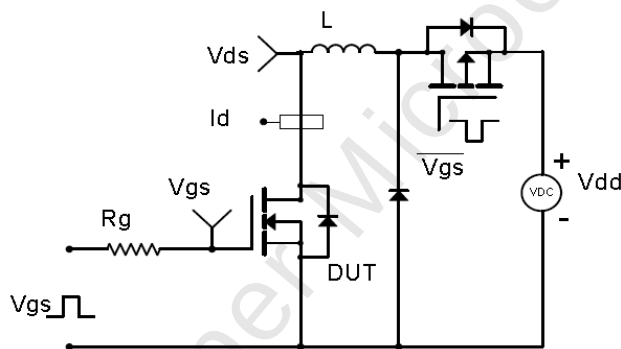
Gate Charge Test Circuit & Waveform



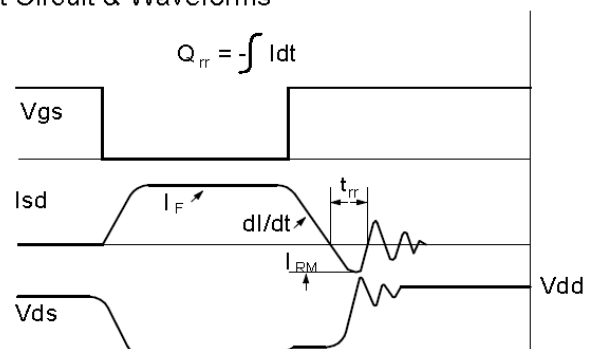
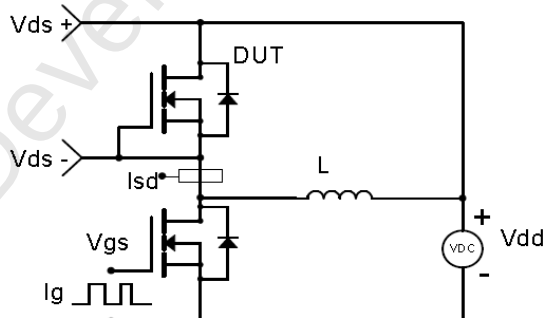
Resistive Switching Test Circuit & Waveforms



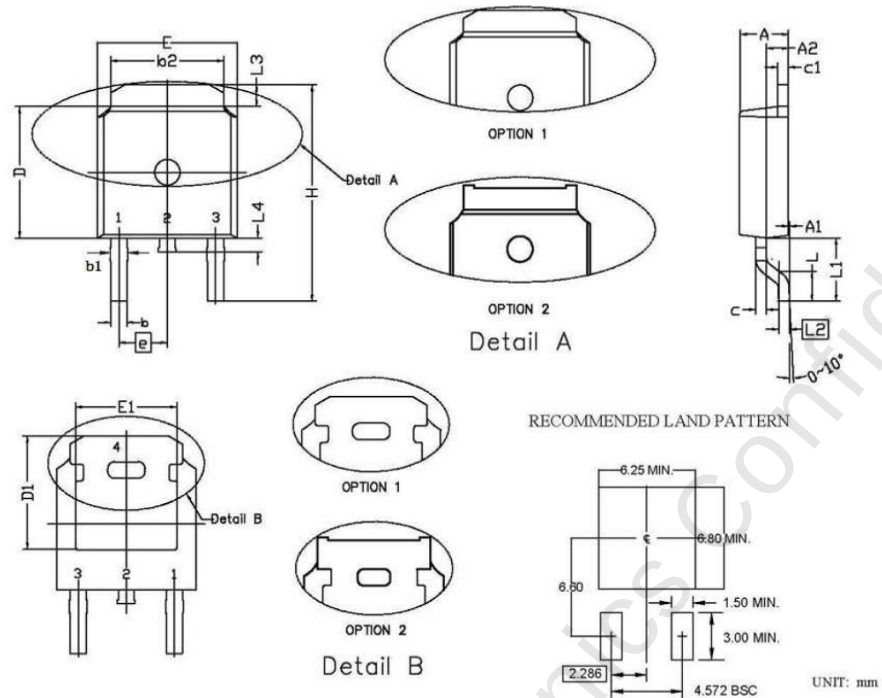
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: TO-252



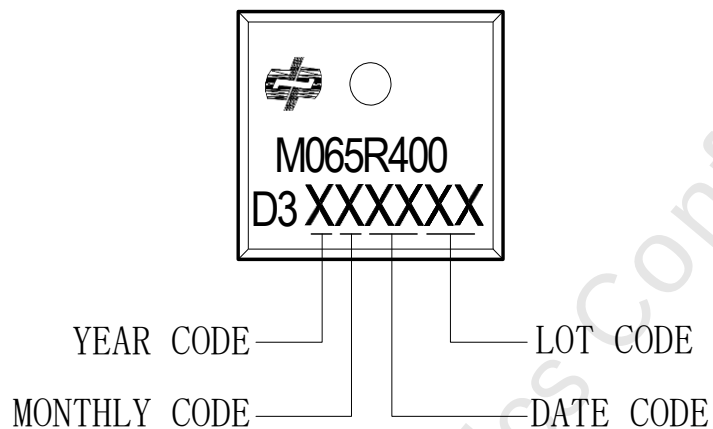
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.15	2.45	0.085	0.096
A1	0.00	0.15	0.000	0.006
A2	0.76	1.36	0.030	0.054
b	0.60	0.91	0.024	0.036
b1	0.65	1.15	0.026	0.045
b2	5.00	5.64	0.197	0.222
c	0.45	0.61	0.018	0.024
c1	0.36	0.66	0.014	0.026
D	5.80	6.30	0.228	0.248
D1	5.00	6.00	0.197	0.236
e	2.29 BSC.		0.090 BSC.	
E	6.30	6.90	0.248	0.272
E1	4.55	5.30	0.179	0.209
H	9.40	10.48	0.370	0.413
L	1.18	1.70	0.046	0.067
L1	2.92 REF		0.115 REF	
L2	0.36	0.66	0.014	0.026
L3	0.72	1.35	0.028	0.053



L4	0.60	1.20	0.024	0.047
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Developer Microelectronics Confidential

Part Marking Information



Revision History

Revision	Major changes
1.05	Release for formal version

重要声明Important Notice

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